



**浩畅半导体**  
www.szhaochang.cn

**BA V19W/BAV20W/BAV21W**

Silicon Epitaxial Planar Diode

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客户确认：

公司签章：

部门

工程部

品保部

采购部

签名

日期



# BAV19W/BAV20W/BAV21W

## Silicon Epitaxial Planar Diode

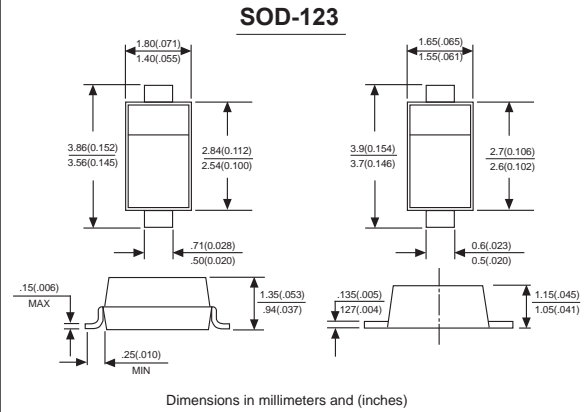
### FEATURES

- Fast Switching Speed
- Surface Mount Package Ideally Suited For Automatic Insertion
- For General Purpose Switching Applications
- High Conductance

### APPLICATIONS

- Surface mount fast switching diode

### ORDERING INFORMATION



Type No.	Marking	Package Code
BAV19W AA	A8	SOD- F23
BAV20W AA	T2	SOD- F23
BAV21W AA	T3	SOD- F23

### MAXIMUM RATING @ Ta=25°C unless otherwise specified

Characteristic S	ymbol	BAV19W	BAV20W	BAV21W	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	120	200	250	V
Working Peak Reverse Voltage	$V_{RWM}$	100	150	200	V
DC Reverse Voltage	$V_R$	71	106	141	V
RMS Reverse Voltage	$V_{R(RMS)}$	71	106	141	V
Average Rectified Output Current	$I_o$	200			mA
Non-Repetitive Peak Forward Surge Current	$I_{FSM}$	2.5			A
@t=1.0 μs					
@t=1.0 s	$I_{FSM}$	0.5			A
Repetitive Peak Forward Surge Current	$I_{FRM}$	625			mA
Power Dissipation	$P_d$	200			mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625			°C/W
Operating and Storage Temperature Range	$T_j, T_{STG}$	-65 to +150			°C

# BAV19W/BAV20W/BAV21W

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Characteristic S	ymbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage BAV19W BAV20W BAV21W	$V_{(BR)R}$	120 200 250		V	$I_R=100\mu A$
Forward Voltage	$V_{FM}$	-	1.0 1.25	V	$I_F=100mA$ $I_F=200mA$
Reverse Current BAV19W BAV20W BAV21W	$I_R$	-	0.1 0.1 0.1	$\mu A$	$V_R=100V$ $V_R=150V$ $V_R=200V$
Capacitance between terminals	$C_T$	-	5	pF	$V_R=0, f=1.0MHz$
Reverse Recovery Time	$t_{rr}$	-	50	ns	$I_F=I_R=30mA,$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$

# BA V19W/BAV20W/BAV21W

TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

